

Attorney's Docket No. 5649-835DV

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Lee et al.

Serial No.: To be assigned

Filed: Currently herewith

For: INTEGRATED CIRCUIT DEVICES FORMED THROUGH SELECTIVE
ETCHING OF AN INSULATION LAYER TO INCREASE THE SELF-ALIGNED
CONTACT AREA ADJACENT A SEMICONDUCTOR REGION (as amended)

Date: September 16, 2003

Mail Stop PATENT APPLICATION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Dear Sirs:

Prior to the examination of the above-referenced application, please enter the following amendments below. Applicants provide the present Preliminary Amendment pursuant to the rules stated in revised 37 C.F.R. 1.121 that became effective on July 30, 2003.

In re: Lee et al.
Serial No.: To be assigned
Filed: Currently herewith
Page 2

In the Title:

At the top of pages 1 and 24, please amend the title to read as follows:

~~METHODS FOR FORMING~~ INTEGRATED CIRCUIT DEVICES FORMED THROUGH
SELECTIVE ETCHING OF AN INSULATION LAYER TO INCREASE THE SELF-
ALIGNED CONTACT AREA ADJACENT A SEMICONDUCTOR REGION AND
~~INTEGRATED CIRCUIT DEVICES FORMED THEREBY~~